

NPN SILICON RF TRANSISTOR

DESCRIPTION:

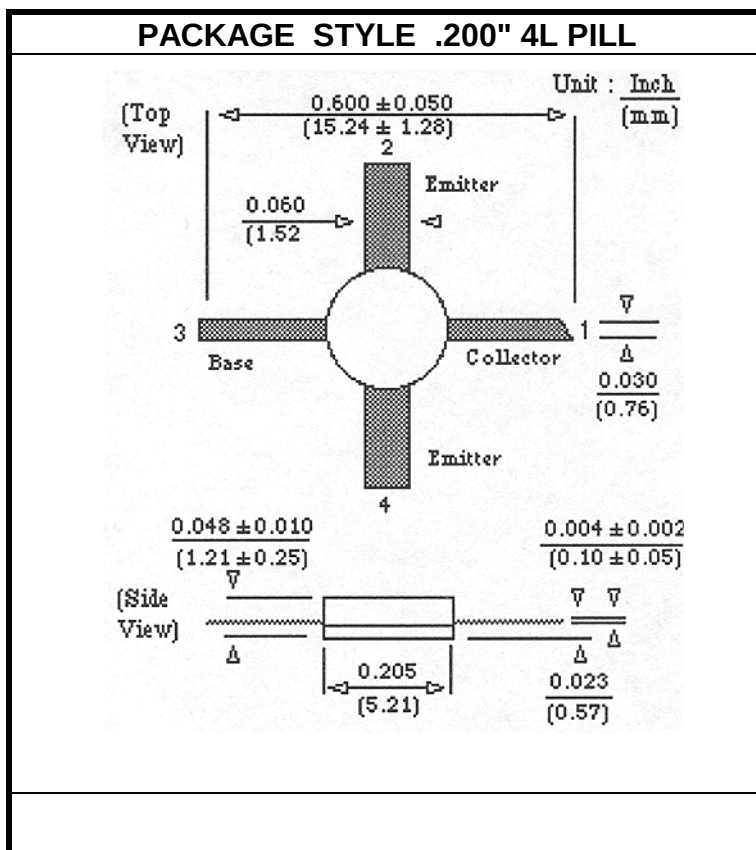
The **MRF313** is Designed for wide band Amplifier Applications up to 400 MHz.

FEATURES:

- $P_G = 15$ dB min. at 1.0 W/ 400 MHz
- Common Emitter for Improved Stability
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	150 mA
V_{CBO}	40 V
V_{CEO}	30 V
V_{EBO}	3.0 V
P_{DISS}	6.1 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	28.5°C/W



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 10$ mA	30			V
BV_{CBO}	$I_C = 0.1$ mA	35			V
BV_{EBO}	$I_E = 1.0$ mA	3.0			V
I_{CEO}	$V_E = 20$ V			1.0	mA
h_{FE}	$V_{CE} = 10$ V $I_C = 100$ mA	20		150	---
C_{OB}	$V_{CB} = 28$ V $f = 1.0$ MHz		3.5	5.0	pF
P_G η_C	$V_{CC} = 28$ V $P_{OUT} = 1.0$ W $f = 400$ MHz	15	16 45		dB %